Peak Repetitive Reverse Voltage $V_{RRM}$ 40VContinuous Forward CurrentIF500mAPeak Repetitive Forward Current, tp ≤ 1msIFRM3.5AForward Surge Current, tp=8msIFSM10APower DissipationPD0.9W*Operating and StorageTJ, Tstg-65 to +150°C	CTLSH05-4M521 SURFACE MOUNT LOW VF SILICON SCHOTTKY DIODE	CECRIPTION: The CENTRAL SEM CTLSH05-4M521 Lo quality Schottky Dioo small size and oper requirements. With 0.9W, and a very smat the SOT-563), this lead dissipating over 3 tir comparable sized su	UCONDUCTOR by V <sub>F</sub> Schott de designed for erational effcie a maximum p all package for adless package nes the power	<b>P.</b> ky Diode or applica ency are power di otprint (cc e design i of simila	tions where the prime ssipation of mparable to s capable of
$\begin{array}{c} \bullet \text{DC/DC Converters} \\ \bullet \text{ Voltage Clamping} \\ \bullet \text{Protection Circuits} \end{array} \\ \bullet \text{ Battery Powered Portable} \\ \text{Equipment} \\ \hline \\ \ \\ \text{Equipment} \\ \hline \\ \ \\ \ \\ \ \\ \ \\ \ \\ \ \\ \ \\ \ \\ \$		<ul> <li>Very Small Package S</li> <li>Current (I<sub>F</sub>=0.5A)</li> <li>Low Forward Voltage</li> </ul>	• Sma Drop		
SYMBOLUNITPeak Repetitive Reverse Voltage $V_{RRM}$ 40VContinuous Forward CurrentIF500mAPeak Repetitive Forward Current, tp ≤ 1msIFRM3.5AForward Surge Current, tp = 8msIFSM10APower DissipationPD0.9W*Operating and StorageJunction TemperatureTJ, Tstg-65 to +150°CThermal Resistance $\Theta_{JA}$ 139°C/W		<ul> <li>DC/DC Converters</li> <li>Voltage Clamping</li> </ul>			Portable
Continuous Forward CurrentIF500mAPeak Repetitive Forward Current, tp ≤ 1msIFRM3.5AForward Surge Current, tp = 8msIFSM10APower DissipationPD0.9W*Operating and StorageTJ, Tstg-65 to +150°CJunction TemperatureTJ, Tstg-65 to +150°C/W	<b>MAXIMUM RATINGS:</b> $(T_A = 25^{\circ}C)$	SYMBOL			UNITS
Peak Repetitive Forward Current, tp $\leq 1 \text{ms}$ I FRM3.5AForward Surge Current, tp=8msIFSM10APower DissipationPD0.9W*Operating and Storage Junction TemperatureTJ, Tstg-65 to +150°CThermal Resistance $\Theta_{JA}$ 139°C/W	Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	40		V
Forward Surge Current, tp=8msIFSM10APower DissipationPD0.9W*Operating and StorageJunction TemperatureTJ, Tstg-65 to +150°CThermal ResistanceΘJA139°C/W	Continuous Forward Current	۱ <sub>F</sub>	500		mA
Power DissipationPD0.9W*Operating and StorageJunction TemperatureTJ, Tstg-65 to +150°CThermal ResistanceΘJA139°C/W	Peak Repetitive Forward Current, tp $\leq$ 1ms	<sup>I</sup> FRM	3.5		А
Operating and Storage Junction TemperatureTJ, Tstg-65 to +150°CThermal Resistance $\Theta_{JA}$ 139°C/W	Forward Surge Current, tp=8ms	<sup>I</sup> FSM	10		А
Junction TemperatureTJ, Tstg-65 to +150°CThermal Resistance $\Theta_{JA}$ 139°C/W	Power Dissipation	PD	0.9		W*
	Junction Temperature	Ũ			°C °C/W*
SYMBOL TEST CONDITIONS MIN MAX UNIT	ELECTRICAL CHARACTERISTICS: (T <sub>A</sub> =25°			MAX	UNITS

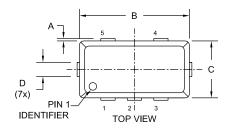
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS	
I <sub>R</sub>	V <sub>R</sub> = 10V		20	μΑ	
I <sub>R</sub>	V <sub>R</sub> = 30V		100	μΑ	
BVR	I <sub>R</sub> = 500μA	40		V	
V <sub>F</sub>	I <sub>F</sub> = 100μA		0.13	V	
V <sub>F</sub> I <sub>F</sub> = 1.0mA			0.21	V	
V <sub>F</sub>	I <sub>F</sub> = 10mA		0.27	V	
V <sub>F</sub> I <sub>F</sub> = 100mA			0.35	V	
V <sub>F</sub> I <sub>F</sub> = 500mA			0.47	V	
C <sub>T</sub> V <sub>R</sub> =1.0V, f=1.0MHz			50	pF	
*FR-4 Epoxy PCB with copper mounting pad area of 33mm <sup>2</sup>		R1 (27	7-April 2006)		

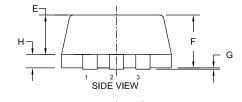


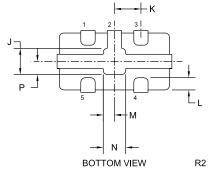
CTLSH05-4M521

## SURFACE MOUNT LOW V<sub>F</sub> SILICON SCHOTTKY DIODE

## **TLM521 CASE - MECHANICAL OUTLINE**

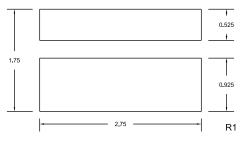




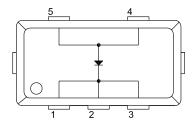


DIMENSIONS						
	INCHES		MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
А		0.005	-	0.125		
В	0.075	0.083	1.900	2.100		
С	0.035	0.043	0.900	1.100		
D	0.007	0.012	0.170	0.300		
E	0.026	0.030	0.650	0.750		
F	0.031	0.039	0.800	1.000		
G	0.000	0.002	0.000	0.050		
Н	0.006	0.010	0.150	0.250		
J	0.013	0.021	0.330	0.530		
К	0.020		0.500			
L	0.004	0.014	0.100	0.350		
М	0.002	0.010	0.060	0.260		
N	0.009	0.017	0.220	0.420		
Р	0.005	0.013	0.120	0.320		
TLM521 (REV: R2)						

Suggested mounting pad layout for maximum power dissipation (Dimensions in mm)



For standard mounting refer to TLM521 Package Details



LEAD CODE:

- 1) CATHODE
- 2) CATHODE
- 3) CATHODE
- 4) ANODE
- 5) ANODE

MARKING CODE: CA

R1 (27-April 2006)